

A study of β -Cu(In,Ga)₃Se₅ effects on Cu(In,Ga)Se₂ thin film solar cells

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Cu(In, Ga)₃Se₅ is known as a β -phase in the phase diagram of Cu₂Se and (In, Ga)₂Se₃. The existence of this phase on the surface of Cu(In, Ga)Se₂ absorber plays an important role for enhancing the performance of Cu(In, Ga)Se₂ solar cells. The energy dispersive x-ray spectroscopy (EDX) is used to investigate and confirm the composition of single Cu(In, Ga)₃Se₅ film and in order to obtain the deposition conditions. In this study, the β -Cu(In, Ga)₃Se₅ with various thicknesses were deposited after a completion of the three-stage co-evaporation process of Cu(In, Ga)Se₂ films. The solar cells with thinner Cu(In, Ga)₃Se₅ showed an increase in open-circuit voltage (V_{oc}). The maximum V_{oc} of 0.707 V was obtained from Cu(In, Ga)₃Se₅ film with 10 nm thick. It is noted here that the conversion efficiencies are slightly lower when compared with the standard three-stage growth solar cells without Cu(In, Ga)₃Se₅. It is mainly due to a decrease in a short circuit current (J_{sc}) and a fill factor (FF). Based on previous studies, the higher V_{oc} was obtained by a larger energy band gap caused by valence band offset at the CdS/CIGS interface.

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